

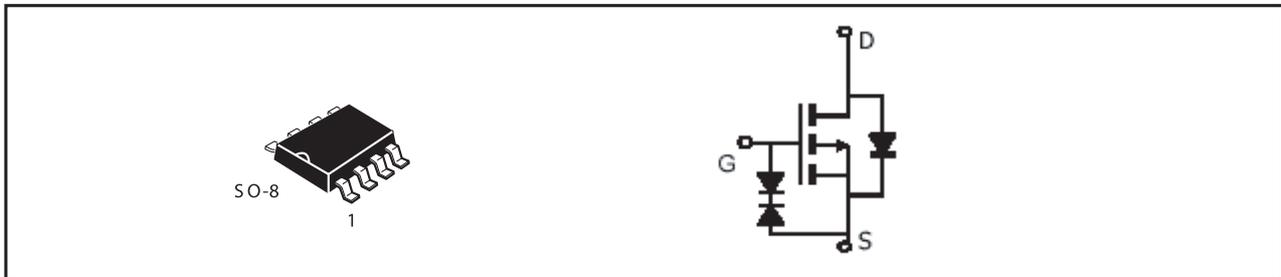


## P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) Max
-35	-14A	8.5 @ V <sub>GS</sub> = -10V
		13 @ V <sub>GS</sub> = -4.0V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-35	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous -Pulsed <sup>b</sup>	I <sub>D</sub>	-14	A
	I <sub>DM</sub>	-56	A
Drain-Source Diode Forward Current	I <sub>S</sub>	-1.7	A
Maximum Power Dissipation	P <sub>D</sub>	2.5	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	50	°C/W
---	------------------	----	------